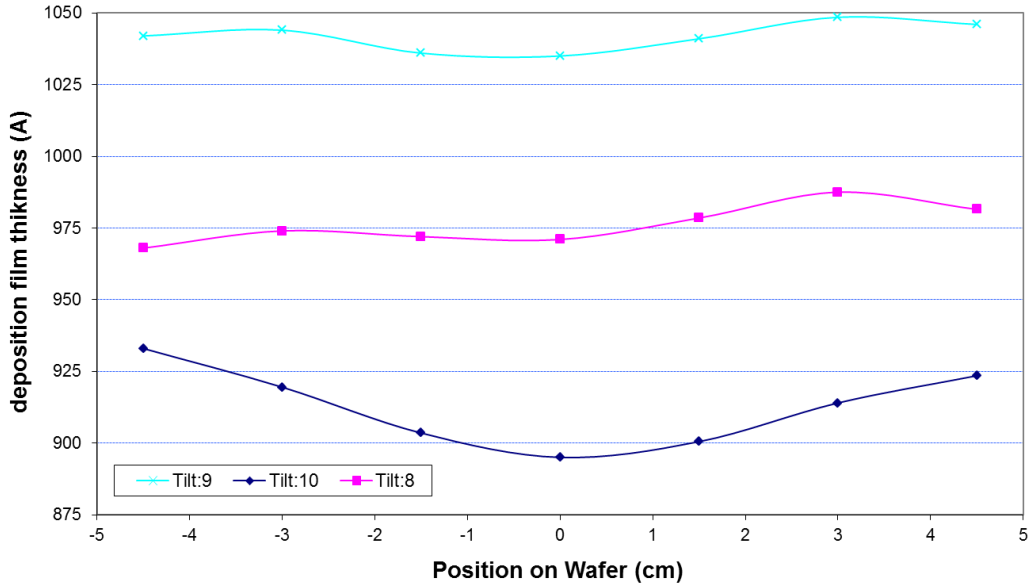


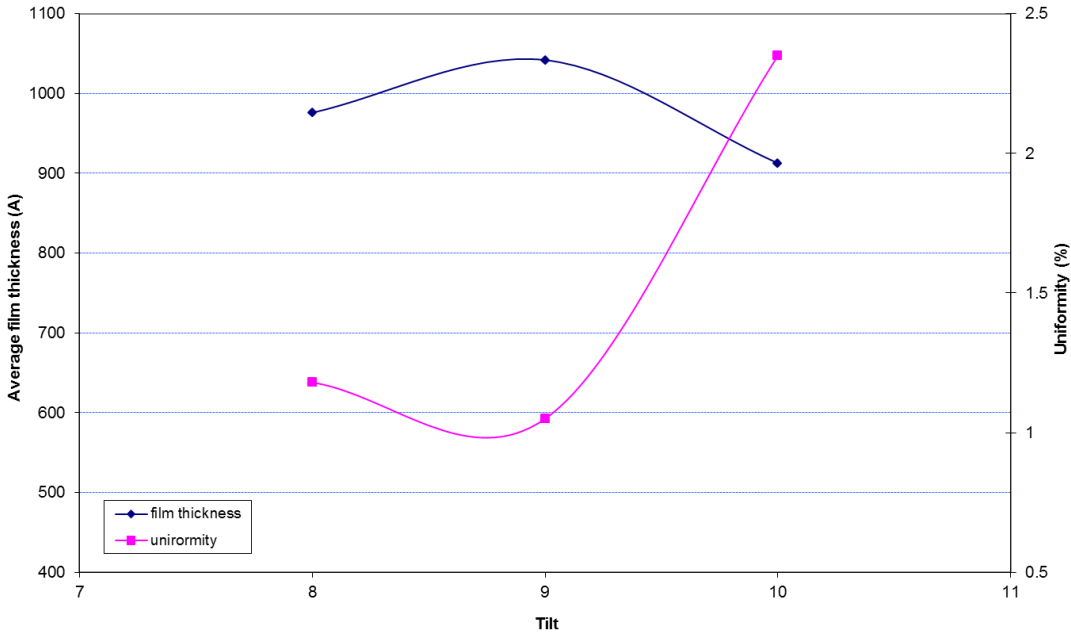
SiO2 Reactive Sputtering – Uniformity and Rate: Sample Position AJA1

Thickness and Uniformity vs Gun Tilt: 1 hour: O2/Ar 5/25sccm; 200W RF; Bias 10W; 3mT; Height 25

SiO2 film thickness vs. Wafer position (Bias:10W; Gun:200W; WD:25; Pressure:3mT; gass flow rate O2/Ar:5/25sccm; time:1h)

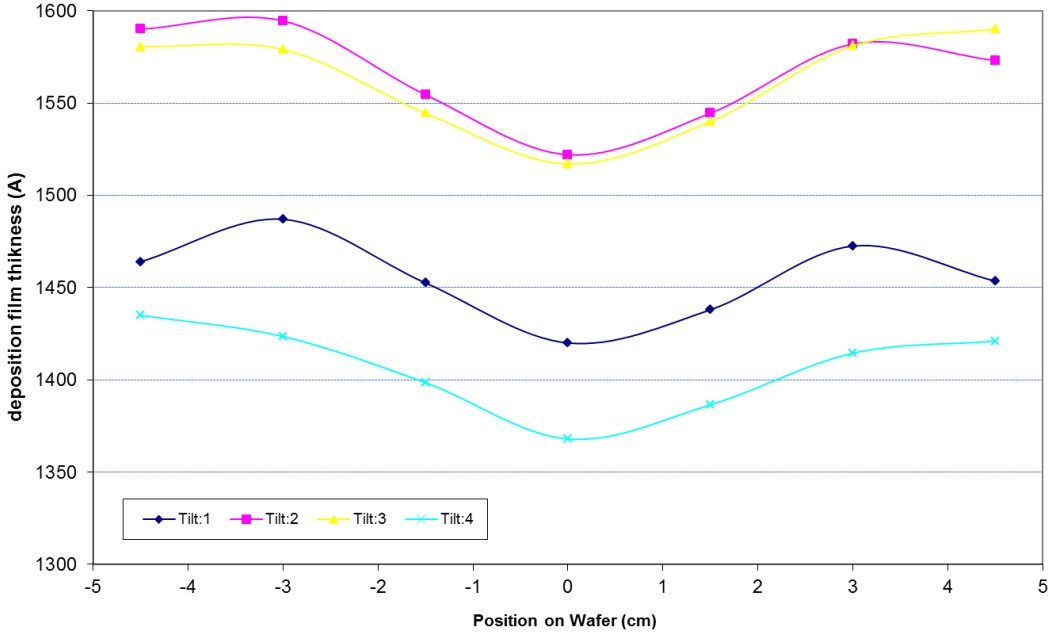


SiO2 film thickness and Uniformity vs. Wafer position (Bias:10W; Gun:200W; WD:25; Pressure:3mT; gass flow rate O2/Ar:5/25sccm; time:1h)



Thickness and Uniformity vs Gun Tilt: 1 hour: O2/Ar 5/25sccm; 200W RF; Bias 10W; 3mT; Height 45

SiO₂ film thickness vs. Wafer position (Bias:10W; Gun:200W; WD:45; Pressure:3mT; gass flow rate O2/Ar:5/25sccm; time:1h)



SiO₂ film thickness and Uniformity vs. Wafer position (Bias:10W; Gun:200W; WD:45; Pressure:3mT; gass flow rate O2/Ar:5/25sccm; time:1h)

